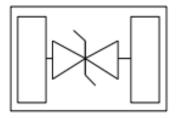


### **Description**

The JE05B1UD10-2L is a bi-directional TVS diode, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive data and power line. The JE05B1UD10-2L complies with the IEC 61000-4-2 (ESD) with  $\pm 30~\rm kV$  air and  $\pm 30~\rm kV$  contact discharge. It is assembled into an ultra-small 0.6x0.3x0.3mm lead-free DFN package. The small size and high ESD surge protection make JE05B1UD10-2L an ideal choice to protect cell phone, digital , audio players and many other portable applications.

### **Circuit Diagram**



Circuit and Pin Schematic

### **Marking Diagram**



Transparent top view

F:Device Marking Code

#### **Features**

- \* 40W peak pulse power (8/20us)
- Low leakage:nA level
- \* Operating voltage: 5V
- \* Low clamping voltage
- \* One power line protects
- \* Complies with following standards:
  - IEC 61000-4-2 (ESD) immunity test

Air discharge: ±30kV

Contact discharge: ±30kV

- IEC61000-4-5 (Lightning) 4A (8/20μs)
- \* RoHS Compliant
- \* Package: DFN0603-2

### **Applications**

- Notebooks and Handhelds
- \* Peripherals
- Projection TV
- Cellular Handsets and Accessories
- Portable Instrumentation
- Audio Players
- \* High Speed Line: USB1.0/2.0,VGA

### **Ordering Information**

Part Number	Packaging	Reel Size	
JE05B1UD10-2L	10000/Tape & Reel	7 inch	



# Absolute Maximum Ratings (T<sub>A</sub>=25°C unless otherwise specified)

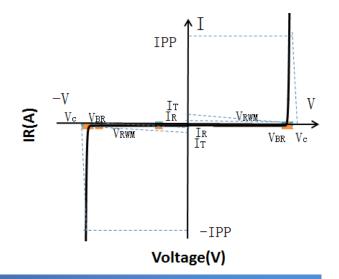
Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20μs)	Ppk	40	W
Peak Pulse Current (8/20μs)	IPP	4	A
ESD per IEC 61000-4-2 (Air)	VESD	±30	kV
ESD per IEC 61000-4-2 (Contact)	VESD	±30	K V
Operating Temperature Range	TJ	-55to +150	°C
Storage Temperature Range	Tstg	-55 to +150	°C

# Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Reverse Working Voltage	Vrwm				5	V
Breakdown Voltage	V <sub>BR</sub>	$I_T = 1 \text{mA}$	6		12	V
Reverse Leakage Current	$I_R$	$V_{RWM} = 5V$		0.001	0.1	uA
Clamping Voltage	Vc	$I_{PP} = 1A (8 \times 20 \mu s \text{ pulse})$		8.7	15	V
Clamping Voltage	Vc	$I_{PP} = 4A (8 \times 20 \mu s \text{ pulse})$		11.2	17.5	V
Junction Capacitance	Сл	VR = 0V, f = 1MHz		10.2	15	pF

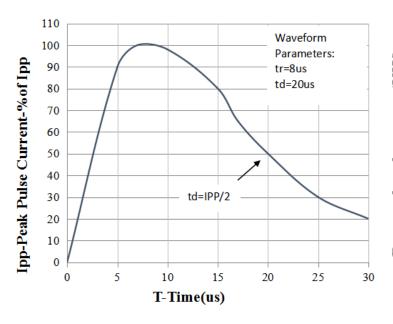
## **Portion Electronics Parameter**

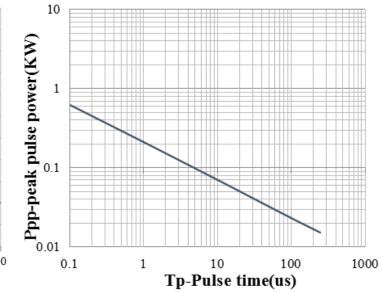
Symbol	Parameter
Iτ	Test Current
Ірр	Maximum Reverse Peak Pulse Current
Vc	Clamping Voltage @Ic





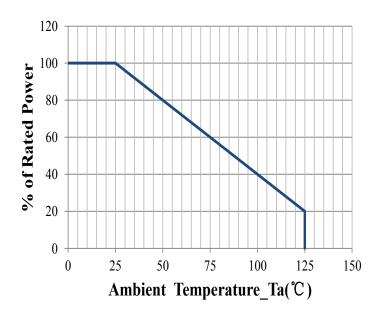
## Typical Performance Characteristics (T<sub>A</sub>=25°C unless otherwise Specified)

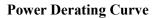


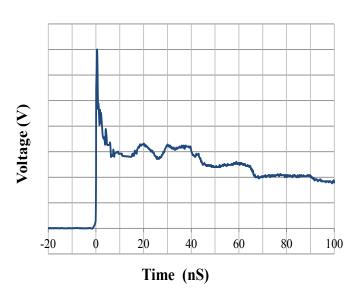


8 X 20us Pulse Waveform

Peak Pulse Power vs. Pulse Time



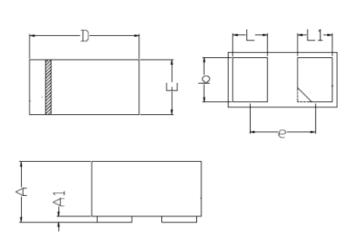




IEC61000-4-2 Pulse Waveform

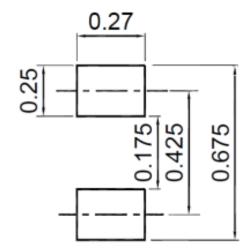


### **DFN0603-2 Package Outline Drawing** (Dimensions in millimeters)



DIM	Millimeters		
DINI	Min	Max	
A	0.230	0.330	
A1	0.000	0.050	
D	0.550	0.650	
E	0.250	0.350	
b	0.215	0.295	
L	0.115	0.225	
L1	0.115	0.225	
e	0.535BSC		

### **Suggested Land Pattern**



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